

Notice of References Cited	Application/Control No. 10/797,945	Applicant(s)/Patent Under Reexamination LIAW, JHON JHY	
	Examiner Andrew O. Arena	Art Unit 2811	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	B	US-6,358,842	03-2002	Zhou et al.	438/633
*	C	US-6,784,096	08-2004	Chen et al.	438/637
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	M	US-			

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	M. Ono et al., "A 40 nm Gate Length n-MOSFET," IEEE Transactions on Electron Devices, Vol. 42, No. 10, October 1995.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.